

electrodes that protrude from the resin layer,

said external connection protruding electrodes forming a bump,

said bump having a height larger than said height of said protruding electrode protruding beyond said resin layer.

110. (Three Times Amended) The semiconductor device as claimed in claim 109, wherein both a side portion of the resin layer and a side portion of the semiconductor element are respectively exposed.

111. (Three Times Amended) A semiconductor device comprising:

a semiconductor element having a surface on which protruding electrodes having convex end portions are formed;

a resin layer formed on the surface of the semiconductor element so as to seal the protruding electrodes except the convex end portions thereof, said convex end portions protruding a height from the resin layer; and

external connection protruding electrodes provided to the convex end portions of the protruding electrodes that protrude from the resin layer,

said external connection protruding electrodes forming a bump,

said bump having a height larger than said height of said protruding electrode protruding beyond said resin layer.

115. (Three Times Amended) A semiconductor device comprising :

a semiconductor element having a surface on which electrode pads connected to an internal part of the semiconductor element and protruding electrodes to be connected to an external part are formed;

lead lines each connecting one of the electrode pads and one of the protruding electrodes so that the protruding electrodes and the internal part are connected through the lead lines; and

a resin layer formed on the surface of the semiconductor element so as to seal the protruding electrodes except end portions thereof,

the protruding electrodes having a core portion and an electrically conductive film formed on a surface of the core portion,

the core portions of the protruding electrodes are directly formed on the lead lines, wherein the core portion comprises an elastic resin.

119. (Three Times Amended) A semiconductor device comprising:

a semiconductor element having a surface on which electrode pads connected to an internal part of the semiconductor element and protruding electrodes to be connected to an external part are formed;

lead lines each connecting one of the electrode pads and one of the protruding electrodes so that the protruding electrodes and the internal part are connected through the lead lines;

a resin layer formed on the surface of the semiconductor element so as to seal the protruding electrodes except end portions thereof which protrude from the resin layer; and

external connection protruding electrodes provided to the end portions of the protruding electrodes that protrude from the resin layer,

the protruding electrodes having a core portion and an electrically conductive film formed on a surface of the core portion,

the core portions of the protruding electrodes are directly formed on the lead lines,

wherein the core portion comprises an elastic resin, and

a part of said protruding electrode sealed by said resin layer and said end portion are covered commonly with said electrically conductive film.

129. (Twice Amended) The semiconductor device as claimed in claim 127, wherein a side surface of the resin layer and a side surface of the semiconductor element are flush with each other.

132. (Amended) A semiconductor device characterized by comprising:

a semiconductor element having protruding electrodes formed on a surface thereof;

a first resin layer that is formed on the surface of the semiconductor element and seals the protruding electrodes except for ends thereof; and

a second resin layer provided so as to cover at least a back surface of the semiconductor element,

a sidewall surface of said semiconductor element being exposed at a sidewall surface of said semiconductor device,

wherein the surface of the semiconductor element is formed with an electronic circuit, and wherein no electronic circuit is formed on a back surface of the semiconductor element.